



# ZXTP2027F

## 60V, SOT23, PNP medium power transistor

### Summary

$V_{(BR)CEV} > -100V$ ,  $V_{(BR)CEO} > -60V$

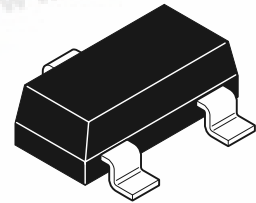
$I_{C(cont)} = -4A$

$R_{CE(sat)} = 31\ m\Omega$  typical

$V_{CE(sat)} < -60\ mV$  @ -1A

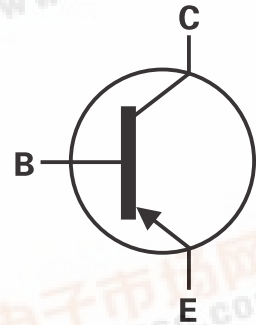
$P_D = 1.2W$

Complementary part number: ZXTN2018F



### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

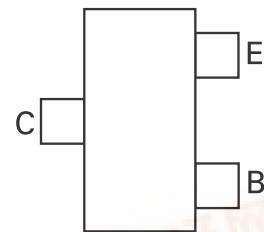


### Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 100V forward blocking voltage

### Applications

- MOSFET and IGBT gate driving
- Motor drive
- Relay, lamp and solenoid drive
- High side switches



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP2027FTA	7	8mm	3,000

### Device marking

951



# ZXTP2027F

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	-100	V
Collector-emitter voltage	$V_{(BR)CEV}$	-100	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-7	V
Peak pulse current	$I_{CM}$	-10	A
Continuous collector current <sup>(b)</sup>	$I_C$	-4	A
Base current	$I_B$	-1	A
Power dissipation @ $T_A=25^{\circ}C^{(a)}$ Linear derating factor	$P_D$	1.0 8.0	W mW/°C
Power dissipation @ $T_A=25^{\circ}C^{(b)}$ Linear derating factor	$P_D$	1.2 9.6	W mW/°C
Power dissipation @ $T_A=25^{\circ}C^{(c)}$ Linear derating factor	$P_D$	1.56 12.5	W mW/°C
Operating and storage temperature	$T_j:T_{stg}$	-55 to +150	°C

## Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R\theta_{JA}$	125	°C/W
Junction to ambient <sup>(b)</sup>	$R\theta_{JA}$	104	°C/W
Junction to ambient <sup>(c)</sup>	$R\theta_{JA}$	80	°C/W

### NOTES:

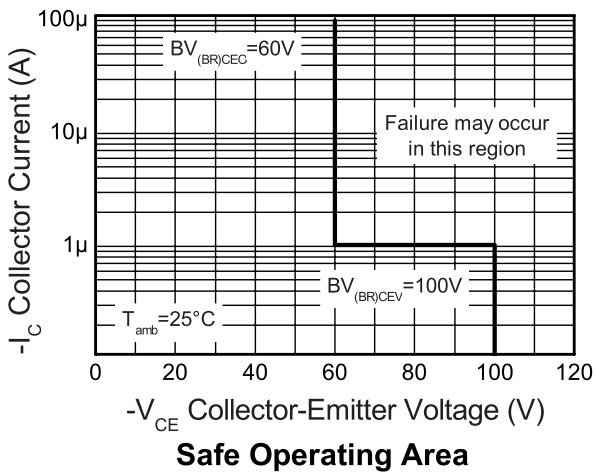
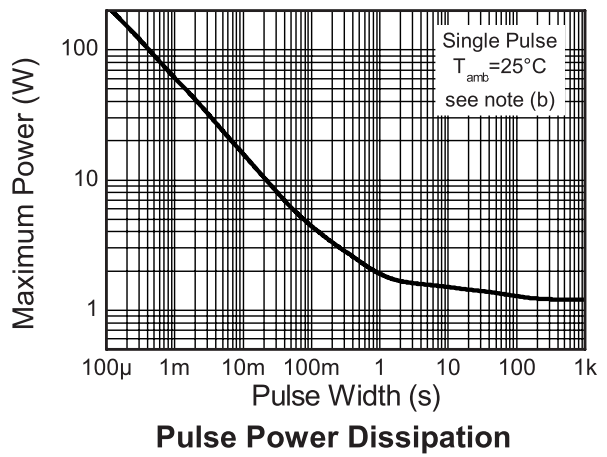
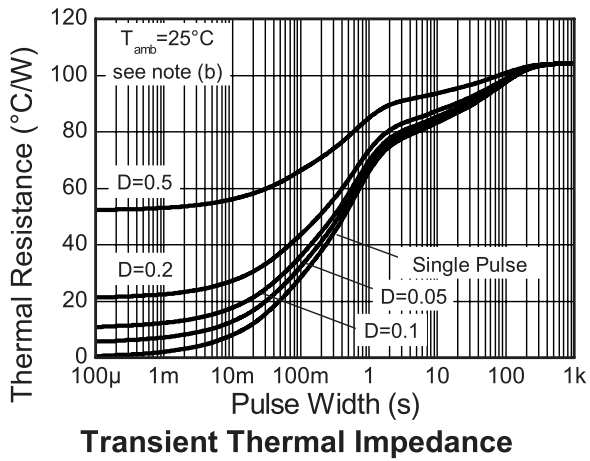
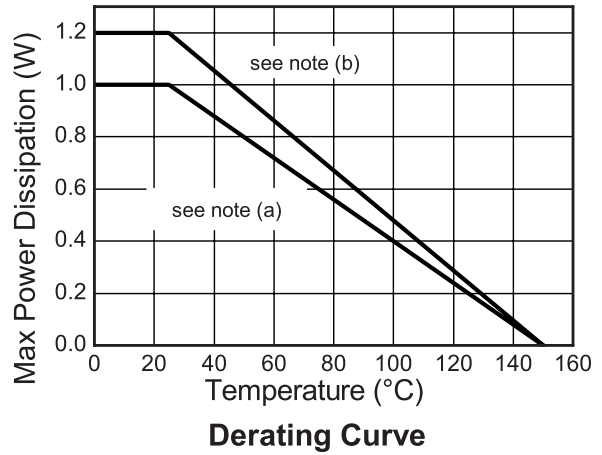
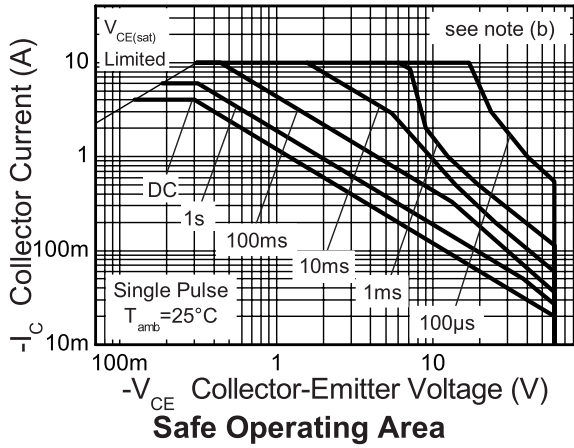
(a) Mounted on 18mm x 18mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(b) Mounted on 30mm x 30mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(c) As (b) above measured at  $t < 5$ secs.

# ZXTP2027F

## Characteristics



# ZXTP2027F

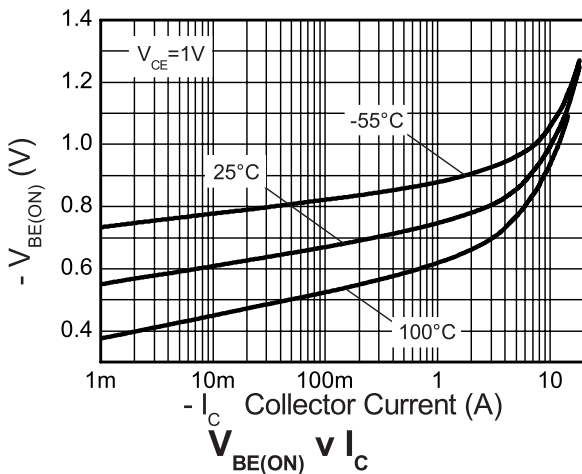
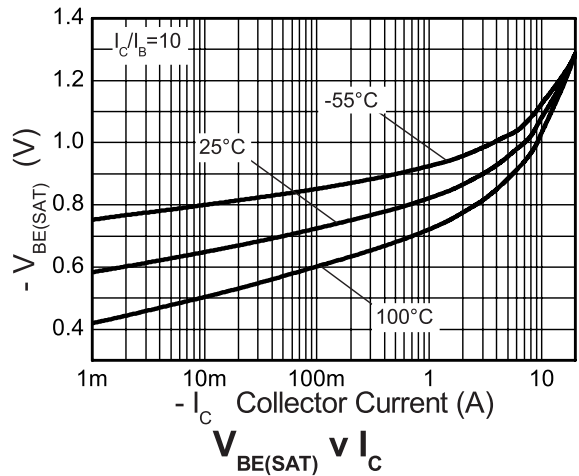
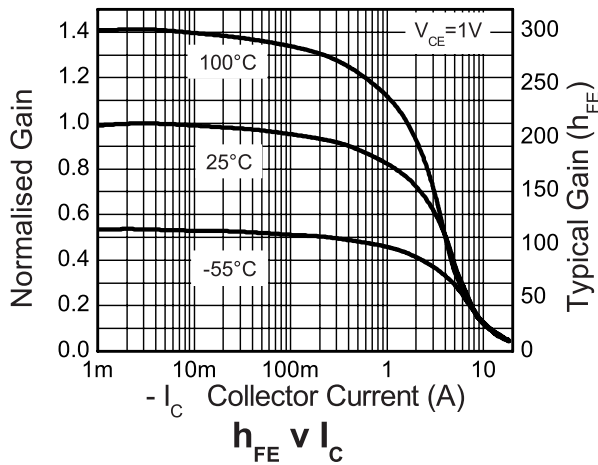
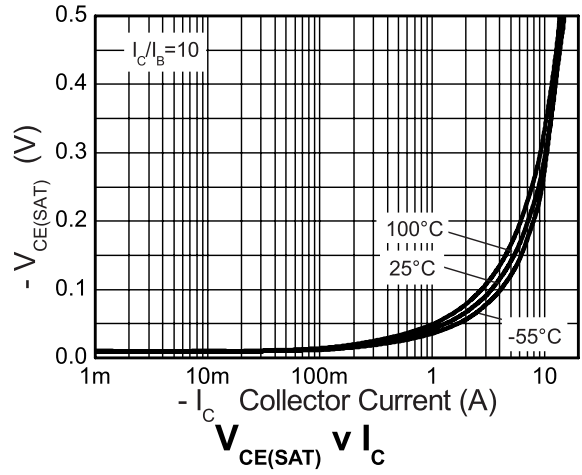
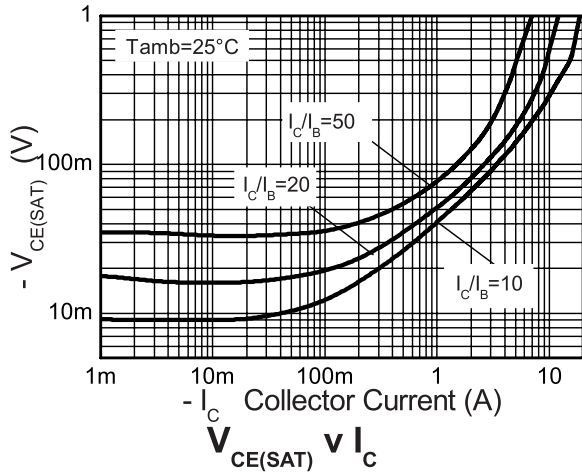
## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-100	-120		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(BR)CEV}$	-100	-120		V	$I_C = -1\mu\text{A}$ , $1V > V_{BE} > -0.3V$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-60	-75		V	$I_C = -10\text{mA}^{(a)}$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-7.0	-8.2		V	$I_E = -100\mu\text{A}$
Collector-emitter cut-off current	$I_{CEV}$			-20	nA	$V_{CE} = -80V$ , $V_{BE} = 1V$
Collector-base cut-off current	$I_{CBO}$			-20	nA	$V_{CB} = -80V$
Emitter-base cut-off current	$I_{EBO}$			-10	nA	$V_{EB} = -6V$
Static forward current transfer ratio	$H_{FE}$	100 100 80 20	250 200 145 40	300		$I_C = -10\text{mA}$ , $V_{CE} = -2V^{(a)}$ $I_C = -2A$ , $V_{CE} = -2V^{(a)}$ $I_C = -4A$ , $V_{CE} = -2V^{(a)}$ $I_C = -10A$ , $V_{CE} = -2V^{(a)}$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		-15 -45 -70 -155	-25 -60 -95 -240	mV mV mV mV	$I_C = -100\text{mA}$ , $I_B = -10\text{mA}^{(a)}$ $I_C = -1A$ , $I_B = -100\text{mA}^{(a)}$ $I_C = -2A$ , $I_B = -200\text{mA}^{(a)}$ $I_C = -4A$ , $I_B = -200\text{mA}^{(a)}$
Base-Emitter saturation voltage	$V_{BE(SAT)}$		-0.89	-1.0	V	$I_C = -4A$ , $I_B = -200\text{mA}^{(a)}$
Base-Emitter turn-on voltage	$V_{BE(on)}$		-0.81	-0.95	V	$I_C = -4A$ , $V_{CE} = -2V^{(a)}$
Transition frequency	$f_T$		165		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -10V$ , $f = 50\text{MHz}$
Output capacitance	$C_{obo}$		44		pF	$V_{CB} = -10V$ , $f = 1\text{MHz}$
Turn-on time	$t_{(on)}$		32		ns	$V_{CC} = -10V$ , $I_C = -2A$ ,
Turn-off time	$t_{(off)}$		305		ns	$I_{B1} = I_{B2} = -200\text{mA}$

### NOTES:

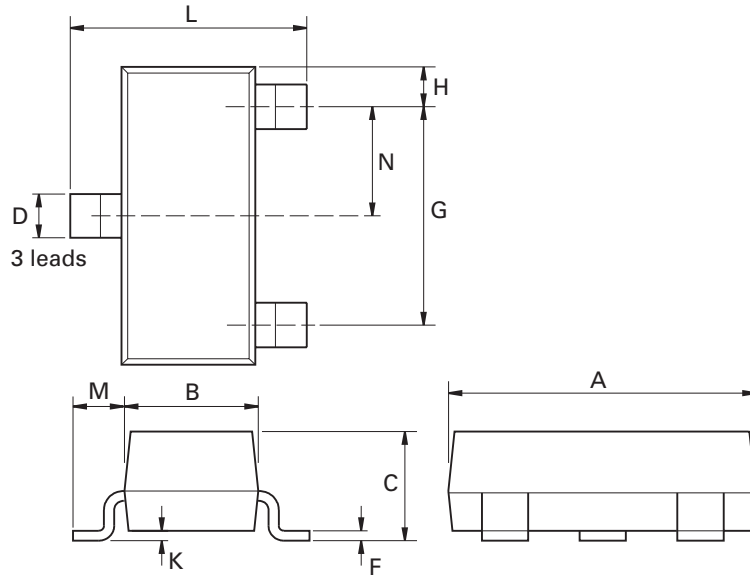
(a) Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

## Typical characteristics



# ZXTP2027F

## Packaging details - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches.

### Europe

Zetex GmbH  
Streitfeldstraße 19  
D-81673 München  
Germany

Telefon: (49) 89 45 49 49 0  
Fax: (49) 89 45 49 49 49  
europe.sales@zetex.com

### Americas

Zetex Inc  
700 Veterans Memorial Highway  
Hauppauge, NY 11788  
USA

Telephone: (1) 631 360 2222  
Fax: (1) 631 360 8222  
usa.sales@zetex.com

### Asia Pacific

Zetex (Asia Ltd)  
3701-04 Metroplaza Tower 1  
Hing Fong Road, Kwai Fong  
Hong Kong

Telephone: (852) 26100 611  
Fax: (852) 24250 494  
asia.sales@zetex.com

### Corporate Headquarters

Zetex Semiconductors plc  
Zetex Technology Park, Chadderton  
Oldham, OL9 9LL  
United Kingdom

Telephone (44) 161 622 4444  
Fax: (44) 161 622 4446  
hq@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contact or be regarded as a representation relating to the products or services concerned. The company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.